

# G1V(A)12C

SIDACs / Uni-directional (G1V Series)

100V, 80A

## Feature

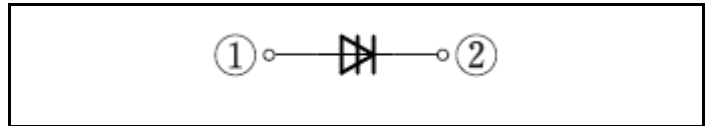
- Uni-directional
- Miniaturized compared to a K1V series
- For pulse generation, DC power with switching operation
- A reliable product with a track record, developed for many applications
- Pb free terminal
- RoHS:Yes

## OUTLINE

Package (House Name): AX06



## Equivalent circuit



## Absolute Maximum Ratings (unless otherwise specified : Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	T <sub>stg</sub>		-40 to 125	°C
Junction temperature	T <sub>j</sub>		125	°C
Maximum off-state voltage	V <sub>DRM(A)</sub>		100	V
RMS on-state current	I <sub>T</sub>	Tl=98°C, 50Hz sine wave, θ=180°	1	A
Pulse on-state current	I <sub>TRM</sub>	Ta=25°C, pulse width 10μs, 60Hz sine wave	80	A
Critical rate of rise of on-state current	di <sub>T</sub> /dt		80	A/μs

\* : See the original Specifications

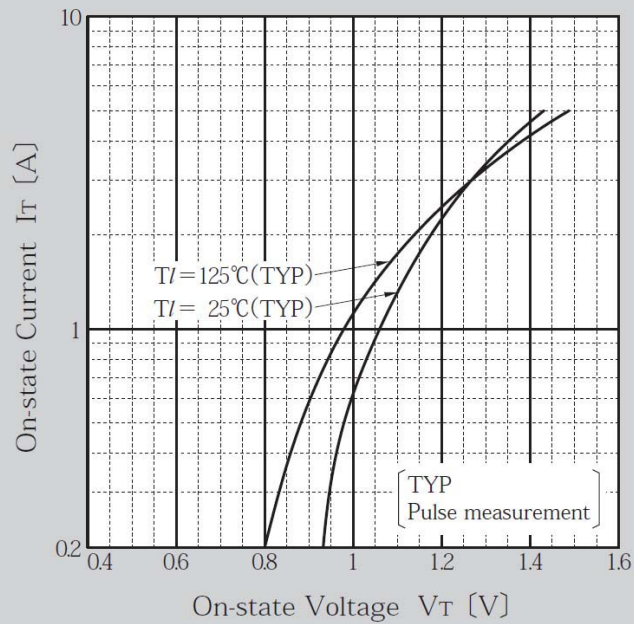
**Electrical Characteristics** (unless otherwise specified : Tl=25°C)

Item	Symbol	Conditions	Ratings			Unit
			MIN	TYP	MAX	
Breakover voltage	$V_{BO(A)}$	Pulse measurement, $dv/dt=4V/ms$	110		130	V
Off-state current	$I_{DRM(A)}$	$V_D=100V$			10	$\mu A$
Breakover current	$I_{BO(A)}$				0.5	mA
Holding current	$I_{H(A)}$				60	mA
Holding current	$I_{H(K)}$				60	mA
On-state voltage	$V_{T(A)}$	$I_T=1A$			1.5	V
On-state voltage	$V_{T(K)}$	$I_T=1A$			1.5	V
Switching resistance	$R_{S(A)}$		0.1			$k\Omega$
Thermal resistance	$R_{th(j-l)}$	Junction to lead			20	$^{\circ}C/W$

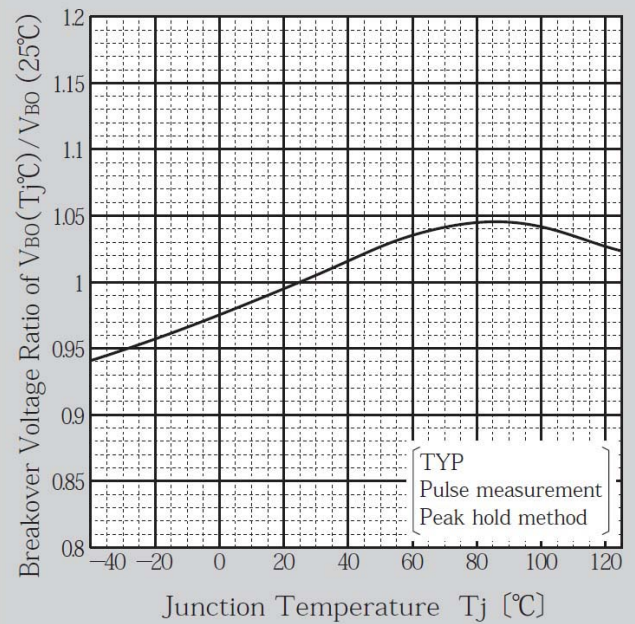
※ :See the original Specifications

# CHARACTERISTIC DIAGRAMS

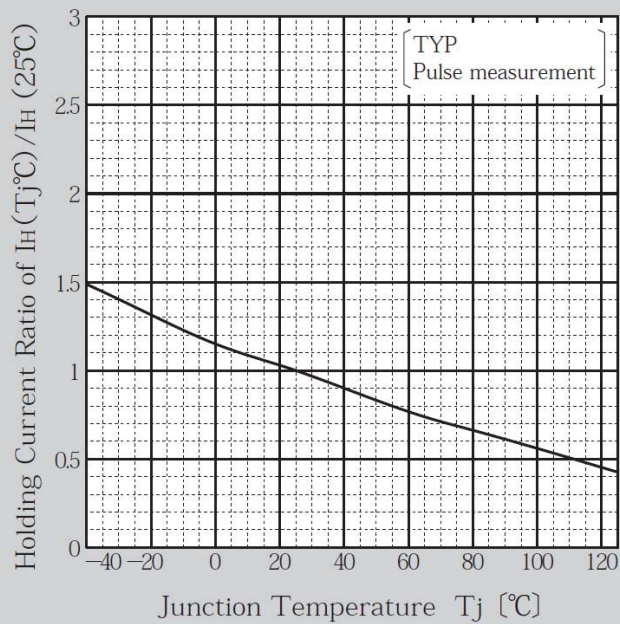
### On-state Voltage vs On-state Current



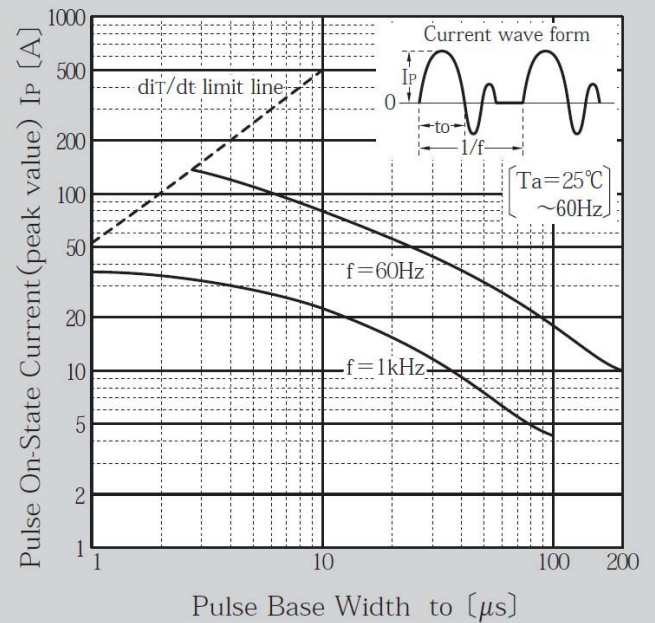
### Breakover Voltage vs Junction Temperature



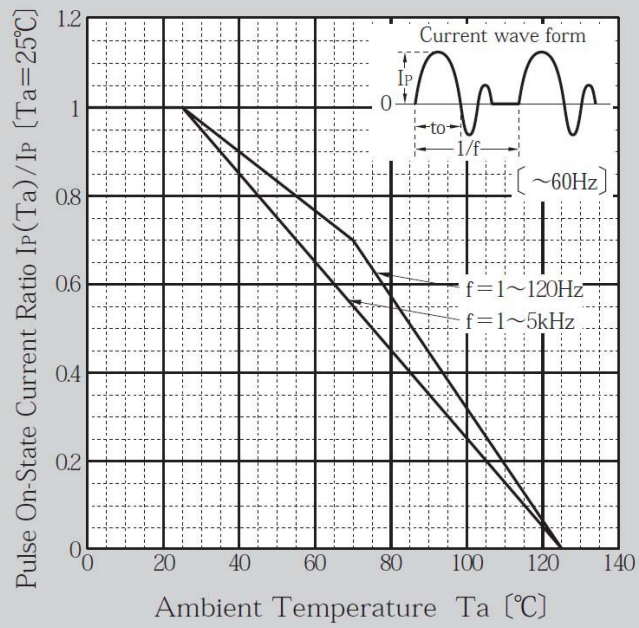
### Holding Current vs Junction Temperature



### Pulse On-state Current Rating ( $I_{TRM}$ )



### Pulse On-state Current Derating (I<sub>TRM</sub>)



# Outline Dimensions

unit:mm

scale: 2/1

## A2

JEDEC Code	—
JEITA Code	—
House Name	AX06

